

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

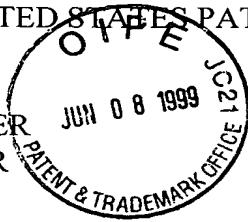
In re Application of:

MARK I. GARDNER  
MARK C. GILMER

Serial No.: 09/079,759

Filed: May 15, 1998

For: METHOD OF MAKING AN  
ADVANCED ISOLATION  
STRUCTURE FOR HIGH DENSITY  
SEMICONDUCTOR DEVICES  
(as amended)



Examiner: A. Mai

Group Art Unit: 2814

Att'y Docket: 2000.002600/TT2587

*Amend*  
6/13  
6-11-99  
RECEIVED  
JUN 11 1999  
TECHNOLOGY CENTER 2001

**RESPONSE TO OFFICE ACTION DATED APRIL 6, 1999**

Assistant Commissioner for Patents  
Washington, D.C. 20231

Sir:

**CERTIFICATE OF MAILING**

I hereby certify that this paper or fee is being deposited with the United States Postal Service with sufficient postage as "FIRST CLASS MAIL" addressed to: Assistant Commissioner for Patents, Washington, DC 20231, this 1<sup>st</sup> day of June, 1999.

  
Signature

This paper is submitted in response to the Office Action dated April 6, 1999 for which the date for response is July 6, 1999.

**IN THE CLAIMS**

Please amend claims 20 and 28 as follows:

20. (amended) A method for forming an isolation trench in a semiconductor

substrate, said substrate having a surface, the method comprising:

*BA*  
forming a first recess in said substrate, said first recess having a first width of at  
most about 3000 Å and extending a first depth beneath the surface of said  
substrate;